



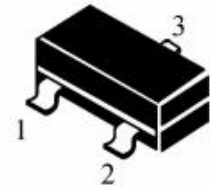
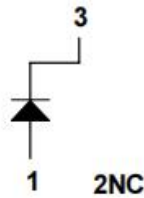
# 安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

MMBD4448

## SOT-23 Switching Diode 开关二极管

### Internal Configuration 内部结构



### Features 特点

Characteristic 特性参数	Symbol 符号	Max 最大值	Unit 单位
Power dissipation 耗散功率	$P_D(T_a=25^\circ\text{C})$	350	mW
Forward Current 正向电流	$I_F$	250	mA
Reverse Voltage 反向电压	$V_R$	75	V
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	-55to+150°C	

### Device Marking 产品打标

MMBD4448=KA3

### Electrical Characteristics 电特性

( $T_A=25^\circ\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^\circ\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压 ( $I_R=100\mu\text{A}$ )	$V_{(BR)}$	75	—	V
Reverse Leakage Current( $V_R=20\text{V}$ ) 反向漏电流( $V_R=75\text{V}$ )	$I_R$	—	25 2.5	nA $\mu\text{A}$
Forward Voltage( $I_F=1\text{mA}$ ) 正向电压( $I_F=10\text{mA}$ ) ( $I_F=50\text{mA}$ ) ( $I_F=150\text{mA}$ )	$V_F$	—	0.715 0.855 1.0 1.25	V
Diode Capacitance 二极管电容 ( $V_R=0\text{V}$ , $f=1\text{MHz}$ )	$C_T$	—	2	pF
Reverse Recovery Time 反向恢复时间	$T_{rr}$	—	4	nS

## ■ Typical Characteristic Curve 典型特性曲线

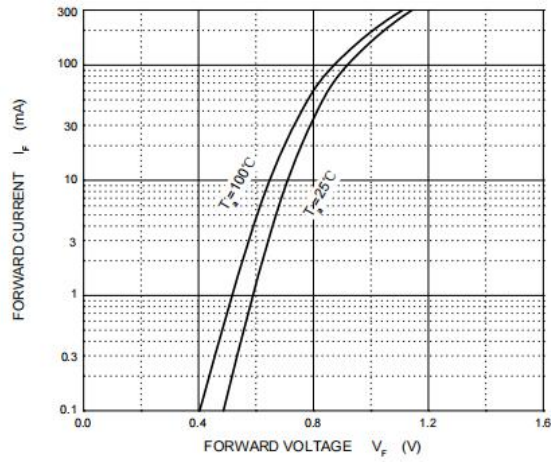


Figure 1: Forward Characteristics

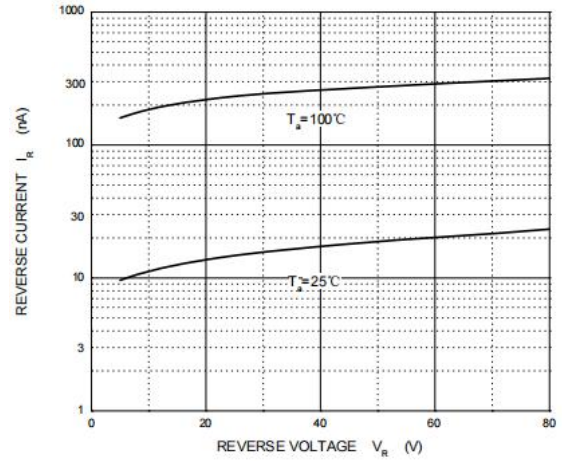


Figure 2: Leakage Current

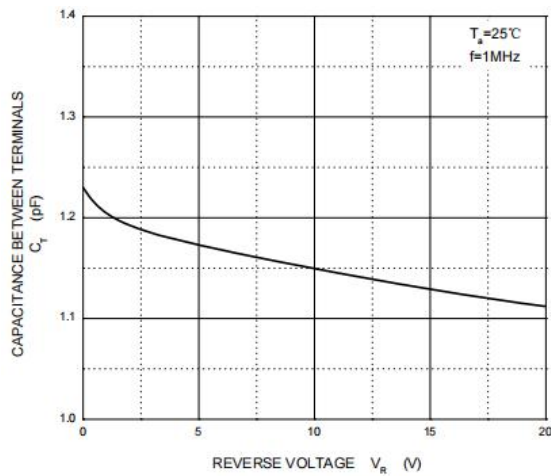


Figure 3: Capacitance Characteristics

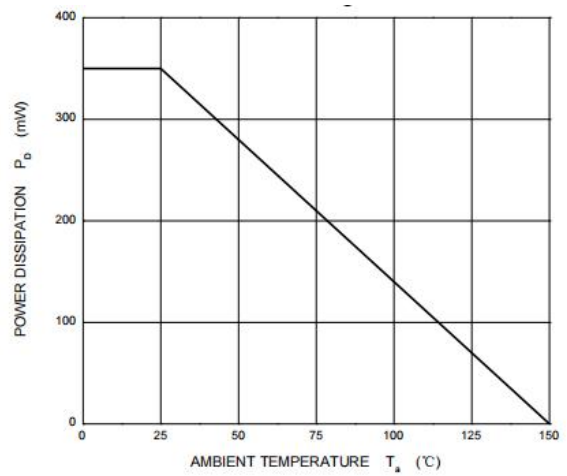
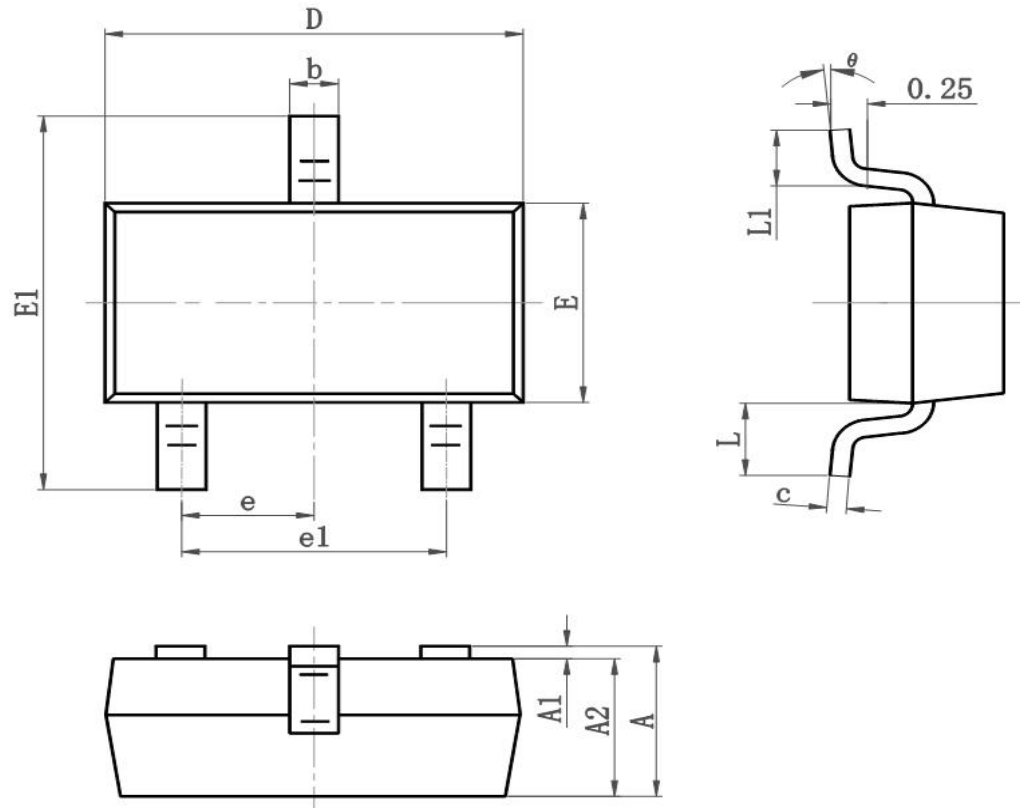


Figure 4: Power Derating Curve

## Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°